

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/716614	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:27
L2	68	semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:30
L3	22	semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:32
L4	4	semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall)) and (memory and nor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:33
L5	3	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))).ti,ab, clm. and (memory and nor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:35
L6	3	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))).ti,ab, clm. and (vertical or vertically or parallel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:37

## EAST Search History

L7	4	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))).ti,ab, clm. and (vertical or vertically or parallel or longitudinal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:38
L8	3	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))) same (vertical or vertically or parallel or longitudinal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:38
L9	3	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))) same (vertical or vertically or parallel or longitudinal or longitudinally)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:38
L10	4	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))) same (vertical or vertically or parallel or longitudinal or longitudinally or direction or orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:39
L11	8	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))) and (vertical or vertically or parallel or longitudinal or longitudinally or direction or orientation) and ((dummy adj electrode) near10 (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:40

## EAST Search History

L12	7	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))) and (vertical or vertically or parallel or longitudinal or longitudinally or direction or orientation) and ((dummy adj electrode) near10 (gate adj electrode) near10 (insulating or dielectric or insulation or oxide or insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:40
L13	2	(semiconductor same substrate same (gate adj electrode) same (dummy adj electrode) same (insulating or dielectric or insulation or insulator or oxide) same (sidewall or side-wall or spacer or (side near wall))) and (vertical or vertically or parallel or longitudinal or longitudinally or direction or orientation) and ((dummy adj electrode) near10 (gate adj electrode) near10 (insulating or dielectric or insulation or oxide or insulator)) and nor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:42

## EAST Search History

L14	150	(US-20020190306-\$ or US-20030003662-\$ or US-20030015742-\$ or US-20020048972-\$ or US-20020153537-\$ or US-20040102008-\$ or US-20040232444-\$ or US-20030012117-\$ or US-20030043520-\$ or US-20040106292-\$ or US-20040056294-\$ or US-20020079596-\$ or US-20030042520-\$ or US-20030107088-\$ or US-20030022422-\$ or US-20030015743-\$ or US-20030098473-\$ or US-20040065926-\$ or US-20030013253-\$ or US-20040142546-\$ or US-20030132464-\$ or US-20020163036-\$ or US-20040159884-\$ or US-20030003666-\$ or US-20020004270-\$ or US-20010026000-\$).did. or (US-20010024857-\$ or US-20020033494-\$ or US-20060027883-\$ or US-20050285206-\$ or US-20050280095-\$ or US-20050167762-\$ or US-20050167739-\$ or US-20050139926-\$ or US-20050052939-\$ or US-20050035397-\$ or US-20050006707-\$ or US-20040245583-\$ or US-20040188726-\$ or US-20040092057-\$ or US-20030111671-\$ or US-20020113257-\$ or US-20020064071-\$ or US-20020058368-\$ or US-20020008293-\$ or US-20010002712-\$).did. or (US-6413861-\$ or US-6387814-\$ or US-6509225-\$ or US-6515338-\$ or US-6548334-\$ or US-6624022-\$ or US-4963501-\$ or US-6455382-\$ or US-6461905-\$ or US-6448608-\$ or US-6670671-\$ or US-6451642-\$ or US-6265292-\$ or US-6054355-\$ or US-6642564-\$ or US-6649955-\$ or US-6657250-\$ or US-6664592-\$ or US-6667199-\$ or US-5698902-\$ or US-6423619-\$ or US-5946563-\$ or US-5010115 + or US-5506606 +	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2006/06/11 15:42
6/11/06 3:47:19 PM C:\Documents and Settings\Erden\My Documents\EAST\Workspaces\10716614_case.wsp						Page 4

## EAST Search History

L15	4	I14 and 257/202	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:43
L16	22	I14 and "257"/\$.ccls. and nor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:43
L17	13	I14 and "257"/\$.ccls. and nor and (dummy adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:44
L18	9	I14 and "257"/\$.ccls. and nor and (dummy adj electrode) and memory.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 15:44